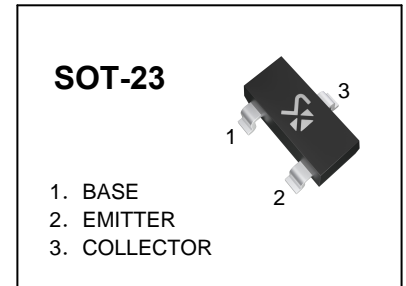


PNP Silicon Epitaxial Planar Transistor

1. Features

- Power dissipation P_{cm} : 0.2 W ($T_{amb}=25^{\circ}C$)
- Collector current I_{cm} : -0.15A
- Collector-base voltage : $V_{(BR)CBO}$: -50V
- Operating and storage junction temperature range T_J , T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



MAXIMUM RATINGS ($T_A=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-150	mA
P_C	Collector Power Dissipation	200	mW
T_j	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature	-55-+150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -0.1mA, I_B = 0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10\mu A, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -50V, I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -6V, I_C = -2mA$	130		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100mA, I_B = -10mA$			-0.3	V
Transition frequency	f_T	$V_{CE} = -10V, I_C = -1mA$	80			MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	L	H
Range	130-200	200-400
Marking	BA	BA

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23

